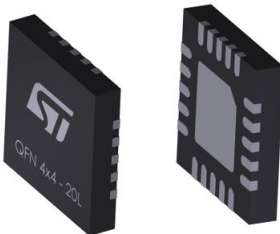


## USB-C PD protection for dual role power (DRP)



QFN-20L 4.0 x 4.0 x 0.75 mm

### Product labels



### Product status link

[TCPP03-M20](#)

### Expansion board

[X-NUCLEO-DRP1M1](#)

### Software example code

[X-CUBE-TCPP](#)

### I2C address

0110 10x (LSB = 'x')

## Features

- USB-IF certified on X-NUCLEO-DRP1M1-G4 (TID6408)
- Embedded gate drivers for N-MOSFET on consumer and provider paths
- 24 V tolerant on VBUS and CC pins
- Integrated discharge on VBUS and VCONN
- Over voltage protection on CC lines against short-to-VBUS
- VBUS current sense analog output through amplifier
- 100 mW OCP and 6 V OVP on VCONN
- Integrated “Dead Battery” management
- Over temperature protection (150 °C typ.)
- I<sup>2</sup>C communication with two I<sup>2</sup>C addresses available
- ECOPACK2, and RoHS compliant

## Complies with the following standards

- UL94, V0
- USB-C power delivery standard 3.1, standard power range (SPR) up to 100 W
- IEC 61000-4-2 level 4 on CC1, CC2 pins:
  - ±8 kV contact discharge
  - ±15 kV air discharge

## Description

The TCPP03-M20 manages power delivery in accordance with USB Power Delivery revision 3.1 up to 100 W (20 V – 5 A, SPR) and PPS for fast charging.

The TCPP03 is a microcontroller companion chip enabling USB Type-C® PD for:

- Dual role power (DRP) or dual role data (DRD)
- Sink configuration when current sense on VBUS is required
- Source configuration.

It provides a solution to interface and protect USB Type-C ports on a power delivery side and has been developed to be used with the STM32 family embedding UCPD (USB Type-C and power delivery).

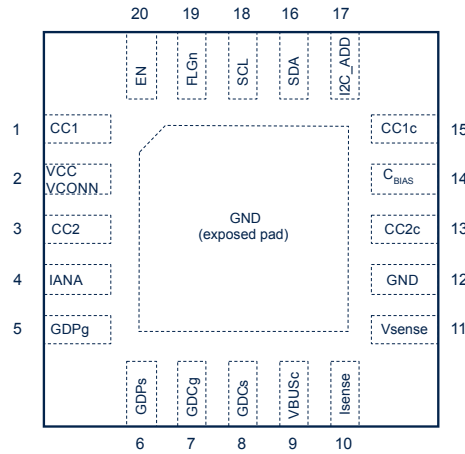
By reusing the STM32 of the application, it is the more cost effective solution as it requires only a few devices to be added:

- The TCPP03 to drive external N-MOSFETs on the VBUS line for consumer and provider paths
- A few discrete devices.

It provides over voltage and over current protections on VBUS and CC pins.

Software is available and could be adapted for other microcontrollers.

# 1 Pinout and functions

**Figure 1. QFN-20L 4.0 x 4.0 x 0.75 mm**

**Table 1. Pinout and functions**

| Name               | Pin # | Type           | Description                                                                   |
|--------------------|-------|----------------|-------------------------------------------------------------------------------|
| CC1                | 1     | Input / output | Configuration channel 1 pin on power delivery controller side.                |
| VCC_VCONN          | 2     | Power          | Power supply for V <sub>CONN</sub> power pin. Connect to 3.3 V or 5.5 V.      |
| CC2                | 3     | Input / output | Configuration channel 2 pin on power delivery controller side.                |
| I <sub>ANA</sub>   | 4     | Output         | V <sub>BUS</sub> current analog measurement.                                  |
| GDPg               | 5     | Output         | Gate driver provider: gate pin of external N-channel MOSFET on source path.   |
| GDPs               | 6     | Input          | Gate driver provider: source pin of external N-channel MOSFET on source path. |
| GDCg               | 7     | Output         | Gate driver consumer: gate pin of external N-channel MOSFET on sink path.     |
| GDCs               | 8     | Input          | Gate driver consumer: source pin of external N-channel MOSFET on sink path.   |
| VBUSc              | 9     | Input          | VBUS connector side.                                                          |
| I <sub>sense</sub> | 10    | Input          | VBUS current measurement.                                                     |
| V <sub>sense</sub> | 11    | Input          | VBUS voltage measurement.                                                     |
| GND                | 12    | GND            | Ground.                                                                       |
| CC2c               | 13    | Input / output | Configuration channel 2 pin on USB Type-C connector side.                     |
| C <sub>BIAS</sub>  | 14    | Output         | ESD capacitor                                                                 |
| CC1c               | 15    | Input / output | Configuration channel 1 pin on USB Type-C connector side.                     |
| I2C_ADD            | 16    | Input          | Least significant bit on I2C address. Connected to GND or 1.8 V / 3.3 V.      |
| SDA                | 17    | Input / output | Serial data line on I2C bus                                                   |
| SCL                | 18    | Input / output | Serial clock line on I2C bus                                                  |
| FLGn               | 19    | Output         | Open-drain output flag (active low). Floating when not connected.             |
| EN                 | 20    | Input          | Enable pin.                                                                   |
| GND                | Pad   | GND            | Ground exposed pad.                                                           |

## 2 Block diagram

Figure 2. Functional block diagram

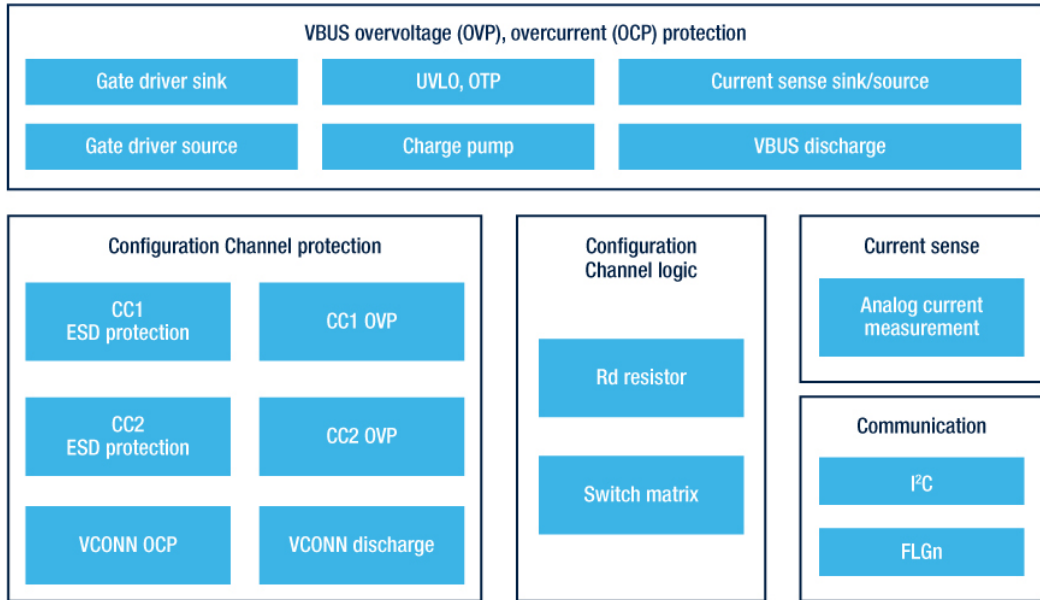
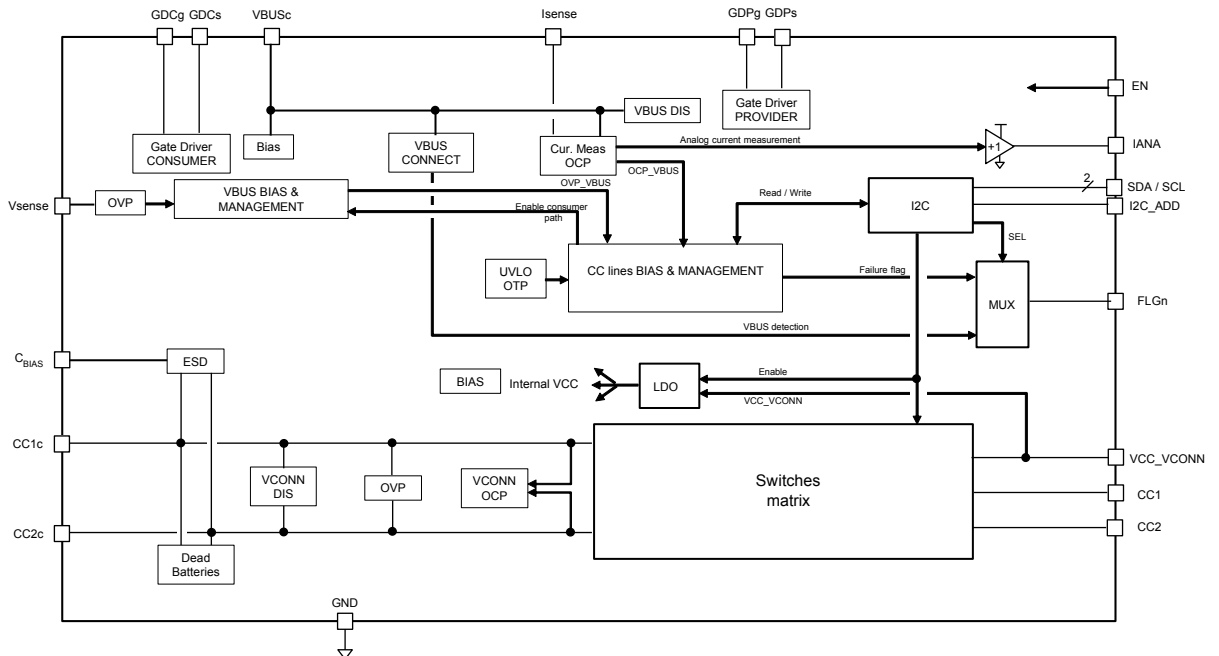
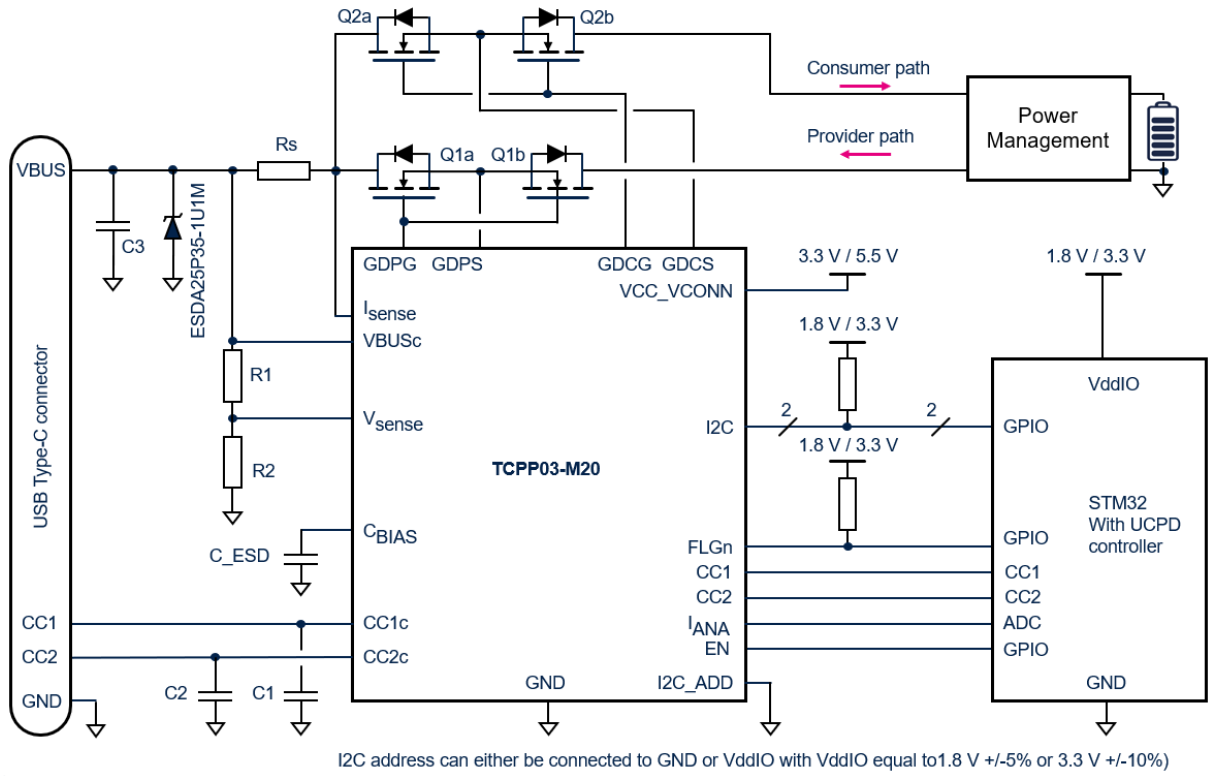


Figure 3. Internal block diagram



### 3 Typical USB-C DRP, DRD application block diagram

Figure 4. Application block diagram example



## 4 Electrical specification

### 4.1 Parameter conditions

Unless otherwise specified:

- All voltages are referenced to GND
- The minimum and maximum values are guaranteed in the worst conditions of operating temperature, supply voltage and frequencies, by tests in production on 100 % of the devices

### 4.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in the tables below, may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

**Table 2. Absolute maximum ratings,  $-40\text{ °C} < T_j < 125\text{ °C}$**

| Symbol             | Parameter                              | Pins                                   | Value       | Unit                 |
|--------------------|----------------------------------------|----------------------------------------|-------------|----------------------|
| $V_{\text{POWER}}$ | Voltage for power pins                 | VCC_VCONN                              | 7           | $V_{\text{DC}}$      |
| $V_{\text{IN}}$    | Voltage for input pins                 | EN, $V_{\text{sense}}$ , I2C_ADD       | 7           |                      |
|                    |                                        | VBUSc, $I_{\text{sense}}$ , GDPs, GDCs | 24          |                      |
| $V_{\text{OUT}}$   | Voltage for output pins                | $I_{\text{ANA}}$ , FLGn                | 7           |                      |
|                    |                                        | $C_{\text{BIAS}}$ , GDPg, GDCg         | 24          |                      |
| $V_{\text{IO}}$    | Voltage for input, output pins         | SDA,SCL, CC1,CC2                       | 7           |                      |
|                    |                                        | CC1c,CC2c                              | 24          |                      |
| $R_{\text{thj-a}}$ | Junction to ambient thermal resistance |                                        | 150         | $^{\circ}\text{C/W}$ |
| $T_{\text{J}}$     | Operating junction temperature range   |                                        | -40 to +125 | $^{\circ}\text{C}$   |
| $T_{\text{STG}}$   | Storage temperature range              |                                        | -55 to +150 | $^{\circ}\text{C}$   |

**Table 3. ESD ratings,  $-40\text{ °C} < T_j < 125\text{ °C}$**

| Symbol             | Description                                                             | Pins       | Value | Unit |
|--------------------|-------------------------------------------------------------------------|------------|-------|------|
| $V_{\text{ESD}_c}$ | System level ESD robustness on USB Type-C connector side <sup>(1)</sup> |            |       |      |
|                    | IEC61000-4-2 Level 4, contact discharge                                 | CC1c, CC2c | 8     | kV   |
|                    | IEC61000-4-2 Level 4, air discharge                                     |            | 15    |      |
| $V_{\text{HBM}}$   | $V_{\text{ESD}}$ ratings human body model (JESD22-A114D, level 2)       | All pins   | 2     | kV   |

1. Internal ESD protection functionality is associated with external capacitor connected on pin  $C_{\text{BIAS}}$ .

### 4.3 Recommended operating conditions

**Table 4. Recommended operating conditions,  $-40\text{ }^{\circ}\text{C} < T_j < 125\text{ }^{\circ}\text{C}$**

| Pins                                               | Min. | Max. | Unit |
|----------------------------------------------------|------|------|------|
| VCC_VCONN, CC1, CC2, V <sub>SENSE</sub>            | 2.7  | 5.5  | V    |
| EN, I <sub>ANA</sub> , I2C_ADD, SDA, SCL, FLGn     | 1.7  | 3.6  | V    |
| CC1c, CC2c, VBUSc, I <sub>SENSE</sub> , GDPs, GDCs | 0    | 22   | V    |

### 4.4 Power supply (VCC\_VCONN, VBUSc)

**Table 5. Electrical characteristics,  $-40\text{ }^{\circ}\text{C} < T_j < 125\text{ }^{\circ}\text{C}$**

| Symbol                 | Parameter                               | Test conditions              | Value |      | Unit |
|------------------------|-----------------------------------------|------------------------------|-------|------|------|
|                        |                                         |                              | Min.. | Max. |      |
| ICC_VCONN              | V <sub>CC</sub> supply current          | Normal mode                  | -     | 2.7  | mA   |
|                        |                                         | Low power mode               | -     | 1    | μA   |
| I <sub>enable</sub>    | Supply current of EN pin <sup>(1)</sup> | Low power mode 1.7 V - 2.7 V | -     | 3    | μA   |
|                        |                                         | Low power mode 2.7 V - 3.6 V | -     | 10   | μA   |
| I <sub>L_VBUSc</sub>   | VBUSc Supply current                    | V <sub>BUSc</sub> = 22 V     | -     | 2    | mA   |
|                        |                                         | V <sub>BUSc</sub> = 5 V      | -     | 0.7  |      |
| t <sub>DIS_VBUSc</sub> | VBUSc discharge time <sup>(2)</sup>     |                              | -     | 220  | ms   |

1. EN pin is dynamically triggered then rise time lower than 50 μs is mandatory.
2. Equivalent discharge resistor is 2.5 kΩ.

### 4.5 VBUS OVP, OCP, gate drivers, current monitoring

**Table 6. Electrical characteristics for V<sub>BUS</sub>,  $-40\text{ }^{\circ}\text{C} < T_j < 125\text{ }^{\circ}\text{C}$**

| Symbol                         | Parameter                                                         | Test conditions                      | Value |      |      | Unit |
|--------------------------------|-------------------------------------------------------------------|--------------------------------------|-------|------|------|------|
|                                |                                                                   |                                      | Min.  | Typ. | Max. |      |
| VBUS_UVLO                      | VBUS under voltage lock out                                       |                                      | 1.9   | 2.4  | 2.9  | V    |
| V <sub>GS</sub>                | Gate to source voltage                                            |                                      | 4.5   | 5    | 5.5  | V    |
| V <sub>OVP_TH</sub>            | OVP V <sub>BUS</sub> threshold voltage                            | Vsense pin voltage                   | 1.1   | 1.16 | 1.25 | V    |
| t <sub>OVP_ON_VBUS</sub>       | OVP V <sub>BUS</sub> turn-on time                                 |                                      |       | 95   | 145  | ns   |
| V <sub>TH_OCP_VBUS</sub>       | V <sub>BUS</sub> OCP threshold voltage                            | Across sense resistor R <sub>s</sub> | 35    | 42   | 45   | mV   |
| t <sub>OFF_OCP_VBUS</sub>      | V <sub>BUS</sub> OCP response time                                |                                      |       | 3    | 8    | μs   |
| I <sub>ana_gain</sub>          | Current sensing gain                                              |                                      | 39    | 42   | 45   | V/V  |
| V <sub>IANA</sub>              | I <sub>ANA</sub> pin output voltage during OCP event on VBUS line |                                      |       | 1.7  | 1.95 | V    |
| t <sub>ON</sub> <sup>(1)</sup> | V <sub>BUS</sub> turn-on time                                     |                                      |       | 1    | 3    | ms   |

1. t<sub>ON</sub> time can be reduced by addition of CGD capacitor.

## 4.6 CC lines OVP and ESD response

**Table 7. Electrical characteristics,  $-40\text{ }^{\circ}\text{C} < T_j < 125\text{ }^{\circ}\text{C}$** 

| Symbol              | Parameter                                | Test conditions                            | Value |      |      | Unit |
|---------------------|------------------------------------------|--------------------------------------------|-------|------|------|------|
|                     |                                          |                                            | Min.  | Typ. | Max. |      |
| R <sub>ON_CC</sub>  | ON resistance                            | Normal mode                                |       | 0.7  | 1.5  | Ω    |
|                     |                                          | Low power mode                             | 8     | 17   | 28   |      |
| C <sub>ON_CC</sub>  | Equivalent ON capacitance in normal mode | 0 < V <sub>CCxc</sub> < 1.2 V, f = 400 kHz | 40    | 60   | 100  | pF   |
| V <sub>TH_CC</sub>  | OVP threshold voltage                    |                                            | 5.5   | 5.75 | 6    | V    |
| V <sub>MIN</sub>    | Minimum voltage                          | Current on CC1c or CC2c < 60 μA            | 0.7   |      |      | V    |
| R <sub>DB</sub>     | DB resistor                              | Measured with 400 μA on CC1c / CC2c        | 4.1   | 5.1  | 5.6  | kΩ   |
| t <sub>OVP_CC</sub> | OVP response time                        |                                            |       | 60   | 100  | ns   |
| BW <sub>CCx</sub>   | Bandwidth                                | at -3dB and 0 < V <sub>CCxc</sub> < 1.2 V  |       | 10   |      | MHz  |

**Table 8. IEC61000-4-2 ±8 kV contact discharge response**

| TCPP03-M20 and STM32G071 state | ESD   | First peak | V <sub>CL</sub> 30 ns |
|--------------------------------|-------|------------|-----------------------|
| OFF                            | +8 kV | 9.2 V      | 3.3 V                 |
| OFF                            | -8 kV | -7.7 V     | -1.0 V                |
| ON                             | +8 kV | 14.8 V     | 6.3 V                 |
| ON                             | -8 kV | -11.8 V    | -1.5 V                |

*Note:* Measurements are performed on *X-NUCLEO-DRP1M1* board plugged on top of *NUCLEO-G071RB*. Ten ESD discharges are applied on connector (CC1c and CC2c) and voltage measurement is done on MCU side (CC1 and CC2), STM32 is still functional after the ESD discharge.

## 4.7 VCONN OCP

**Table 9. Electrical characteristics,  $-40\text{ }^{\circ}\text{C} < T_j < 125\text{ }^{\circ}\text{C}$** 

| Symbol                  | Parameter                 | Test conditions       | Value |      |      | Unit |
|-------------------------|---------------------------|-----------------------|-------|------|------|------|
|                         |                           |                       | Min.  | Typ. | Max. |      |
| R <sub>ON_VCONN</sub>   | ON resistance             |                       | 2.1   | 3    | 5.5  | Ω    |
| I <sub>VCONN</sub>      | FET max operating current | VCONN = 3.0 V - 5.5 V |       |      | 40   | mA   |
| R <sub>dis-vconn</sub>  | Discharge resistor        |                       | 2.5   | 4    | 5    | kΩ   |
| OCP <sub>TH_VCONN</sub> | OCP threshold             |                       | 40    | 47   | 55   | mA   |
| t <sub>OCP_VCONN</sub>  | OCP response time         |                       |       | 0.9  | 2    | μs   |

## 5 Electrical characteristic curves

Figure 5. VBUS turn-on time ( $t_{ON}$ )

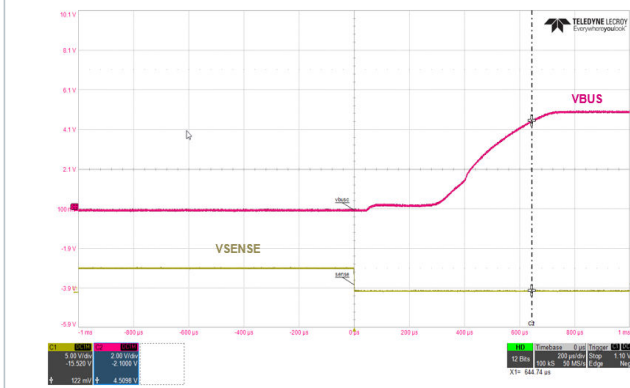
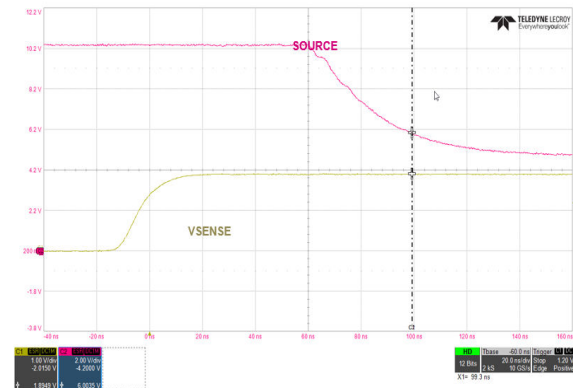
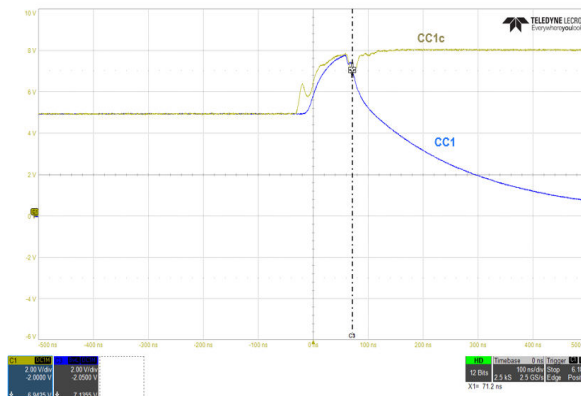


Figure 6. VBUS OVP response time



Note: Test conditions for Figure 5 and Figure 6: TCPP03-M20 is in hibernate mode  $VCC\_VCONN = ENABLE = 0$  V,  $VBUS = 5$  V.

Figure 7. CC line (CC1 or CC2) OVP response time



Note: Test conditions for Figure 7: TCPP03-M20 in normal mode  $VCC\_VCONN = +5$  V,  $ENABLE = 3.3$  V,  $VBUS = 0$  V.



## 6 Functional description

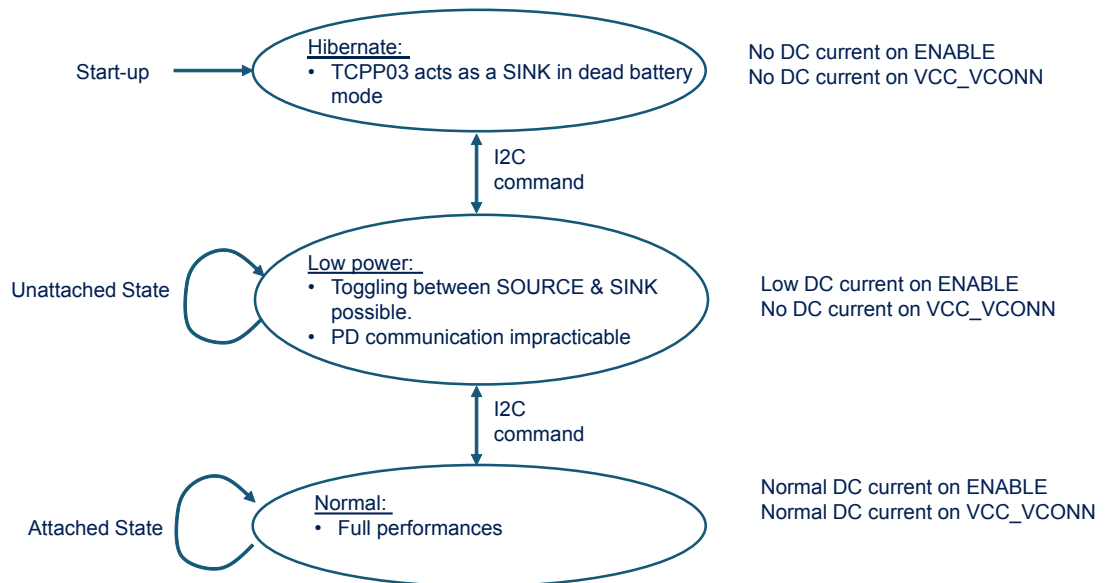
### 6.1 Overview

The TCPP03-M20 is a cost effective solution to protect microcontrollers featuring built-in USB-C power delivery (UCPD) controller or other low voltage power delivery controller. It is especially adapted to dual role power, dual role data applications but also for sink applications requiring a current sense functionality.

### 6.2 Power modes

The TCPP03-M20 embeds three distinct power modes controlled by the UCPD controller via the I2C bus.

**Figure 8. Power mode process**



**Table 10. Power modes versus power supply**

| VCC_VCONN      | ENABLE                      | I <sub>DC</sub><br>VCC_VCONN | I <sub>DC</sub> ENABLE | Mode                | Comments                                                                                                                                            |
|----------------|-----------------------------|------------------------------|------------------------|---------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|
| X              | 0 V                         | 0 μA                         | 0 μA <sup>(1)</sup>    | OFF (reset)         | Dead batteries enabled<br>FLGn indicates VBUS voltage<br>I2C inactive / I2C registers reset                                                         |
| X              | 1.8 V ±5%, or<br>3.3 V ±10% | 0 μA                         | 0 μA <sup>(1)</sup>    | Wake-up / Hibernate | Dead batteries enabled<br>FLGn indicates VBUS voltage<br>I2C active<br>Default state at start-up                                                    |
| X              | 1.8 V ±5%, or<br>3.3 V ±10% | 0 μA                         | < 10 μA <sup>(1)</sup> | Low power           | Dead batteries disabled<br>High ohmic CC => No PD communication possible<br>OVP protection by clamping<br>FLGn indicates VBUS voltage<br>I2C active |
| 2.7 V to 5.5 V | 1.8 V ±5%, or<br>3.3 V ±10% | 2.7 mA                       | < 30 μA <sup>(1)</sup> | Normal              | Dead batteries disabled<br>Full performance mode<br>I2C active<br>FLGn indicates failures                                                           |

1. Dynamic currents of I2C interface have to be added to the values indicated when the I2C bus is used.

**Table 11. TCPP03-M20 states versus power modes**

| Power mode          | CC switches | OVP CC     | Dead batteries | Gate driver consumer | Gate driver provider | OVP VBUS | FLGn          | I2C | I <sub>ANA</sub> | OCP VBUS | V <sub>CONN</sub> VBUS Dis. | Comment                   |
|---------------------|-------------|------------|----------------|----------------------|----------------------|----------|---------------|-----|------------------|----------|-----------------------------|---------------------------|
| OFF                 | OFF         | NA         | ON             | ON <sup>(1)</sup>    | OFF                  | ON       | VBUS connect  | OFF | OFF              | OFF      | OFF                         | TCPP not powered          |
| Wake-up / Hibernate | OFF         | NA         | ON             | Controlled by I2C    | OFF                  | ON       | VBUS connect  | ON  | OFF              | OFF      | OFF                         | Default state at start-up |
| Low power           | High ohmic  | 5 V clamp  | OFF            | Controlled by I2C    | OFF                  | ON       | VBUS connect  | ON  | OFF              | OFF      | OFF                         | Signaling only            |
| Normal              | Full perf.  | Active OVP | OFF            | Controlled by I2C    |                      | ON       | Failure flags | ON  | ON               | ON       | Controlled by I2C           | PD communication active   |

1. Consumer (sink) gate driver is self biased with VBUS<sub>Sc</sub> voltage

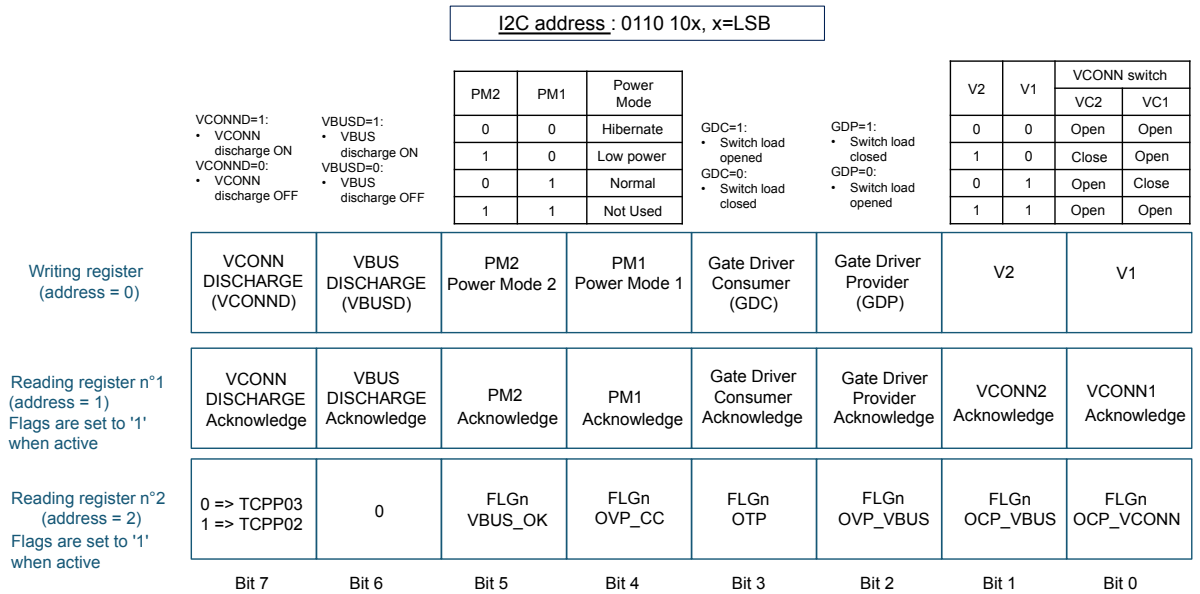
## 6.3 I2C

### 6.3.1 I2C registers

The I2C address used by TCPP03-M20 is 0110 10x, with LSB = 'x'.

The LSB bit of the I2C address is set when connecting TCPP03-M20 pin I2C\_ADD to GND (for LSB = '0') or VddIIO (for LSB = '1').

Figure 9. I2C registers



### 6.3.2 I2C data rate

The I2C slave data rate is limited to 1 Mbps.

## 7 Protection features

TCPP03-M20 embeds protection features for dual role power (DRP), dual role data (DRD) applications, as required by:

- USB-C specification
- USB power delivery specification 3.1
- International electrotechnical commission (IEC)

### 7.1 FLGn pin description

FLGn pin is an open-drain output flag in steady state, it must be left floating when not connected.

In hibernate and low power modes FLGn indicates voltage presence on VBUS.

In normal mode, FLGn indicates an error (OVP, OCP or OTP): I2C registers must be read to identify the error.

Recovery for each error type is described in each section of below paragraphs.

### 7.2 How to protect against ESD (electrostatic discharge) applied on the USB Type-C connector?

Electrostatic discharges can be conducted by the USB Type-C connector and may damage the electronic circuitry of the application.

The TCPP03-M20 integrates ESD protection for CC1 and CC2 lines up to +8 kV contact discharge (IEC 61000-4-2), associated with an external 100 nF - 50 V capacitor on C<sub>BIAS</sub> pin.

### 7.3 VBUS management

An overvoltage protection is required on VBUS when the absolute maximum ratings of your power management integrated circuit is below the maximum voltage that can be applied on VBUS.

Until now, it was common to find the protection circuit inside a controller dedicated to USB-C power delivery. However, by supporting USB-C PD with an embedded module inside an MCU and a companion Type-C port protection device, you can lower your bill of material and facilitate the transition, without requiring an expensive USB-C PD ASIC controller. One of the reasons the MCU and TCPP03-M20 bundle is such a compelling financial proposition is that the latter device integrates the VBUS gate drivers, which enable the use of cost-effective and smaller N-MOSFETs, instead of the P-MOSFETs usually used by ASIC controllers.

This is an added value of TCPP03-M20, specially when the VBUS line is misfed if a defective charger is stuck at a higher voltage than negotiated or a defective cable is inserted.

Overvoltage protection is always required on the VBUS line to prevent against a voltage higher than negotiated on the VBUS.

This use case can occur even when power delivery is not used i.e when the VBUS voltage is 5 V.

#### 7.3.1 VBUS turn-on

VBUS turn-on time after I2C command is achieved in  $t_{ON} = 1$  ms (see Figure 5).

### 7.3.2 VBUS UVLO (under voltage lock out)

This block continuously monitors VBUS voltage. It acts as:

- An UVLO (under voltage lock out) for the VBUS circuitry: OVP\_VBUS and consumer gate driver are enabled once the VBUS voltage reaches VBUS\_UVLO voltage level (2.4 V typ.)
- It signals to the I2C block the presence of a voltage on VBUS when the VBUS voltage reach VBUS\_UVLO voltage level (2.4 V typ.)

### 7.3.3 VBUS OVP turn-on and turn-off

When V<sub>SENSE</sub> pin voltage goes above V<sub>OVP\_TH</sub>, OVP is turned ON in less than 95 ns (t<sub>OVP\_ON\_VBUS</sub> typical value), and FLGn pin goes to 'low-Z' state.

Fast shut-down is enabled by TCPP03-M20 gate driver by shorting the MOSFET gate and source pin. As a result, source pin goes safely to 0 V and I2C register is updated with relevant value.

OVP recovery is ensured after a typical delay of 64 μs: the external power mosfet is turned-on and Flag pin FLGn goes back to Hi-Z state after the end of the OVP condition.

### 7.3.4 How to set TCPP03-M20 OVP threshold according to VBUS maximum voltage allowed by the application

As shown in Figure 4, R1 / R2 bridge gives an image of VBUS voltage to set TCPP03-M20 OVP threshold.

With fixed R1 value (10 kΩ), the table provides R2 values for various TCPP03-M20 OVP threshold according to VBUS maximum voltage allowed by the application.

**Table 12. R2 values versus VBUS OVP threshold when R1 = 10 kΩ**

| R2     | VBUS max. | P max. |
|--------|-----------|--------|
| 2.4 kΩ | 6 V       | 15 W   |
| 1.3 kΩ | 10 V      | 27 W   |
| 976 Ω  | 13 V      | 36 W   |
| 732 Ω  | 17 V      | 45 W   |
| 560 Ω  | 22 V      | 100 W  |

## 7.4 VBUS current sense (IANA pin)

The I<sub>ANA</sub> output pin is active only in normal mode.

The I<sub>ANA</sub> output can be connected directly to the STM32 ADC input because it is internally biased by EN pin.

The I<sub>ANA</sub> output voltage is lower than 1.8 V to be compatible with 1.8 V and 3.3 V MCU I/O.

## 7.5 V<sub>BUS</sub> analog current measurement and bidirectional OCP

The over current protection on VBUS is bidirectional i.e active for both consumer (i.e sink or UFP application) and provider (i.e source or DFP application) power path.

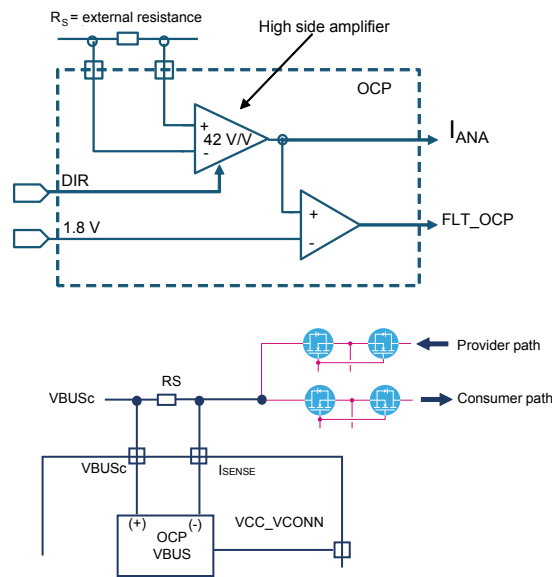
VBUS OCP threshold is set by external serial resistor on VBUS. The gain for the analog reading is set to 42 V/V.

The OCP threshold is set to 0.042 V thanks to Rs.

The OCP VBUS is biased by VCC\_VCONN and works only in normal mode.

Equivalent block diagram in TCPP03-M20 for V<sub>BUS</sub> analog current measurement and OCP is given here after:

**Figure 10. Equivalent block diagram in TCPP03-M20**



**Table 13. Recommended values**

| Typical current | VBUS OCP threshold | Rs - Sense resistor (normalized values) |
|-----------------|--------------------|-----------------------------------------|
| 0.5 A           | 0.9 A              | 47 mΩ                                   |
| 1.5 A           | 1.9 A              | 22 mΩ                                   |
| 3.0 A           | 4.2 A              | 10 mΩ                                   |
| 5.0 A           | 6.0 A              | 7 mΩ                                    |

The OCP is biased continuously: inrush current magnitude is controlled by the user through an external capacitor. Please refer to the [X-NUCLEO-DRP1M1](#) user manual for more informations on external capacitor to control the inrush current magnitude.

If an OCP event occurs:

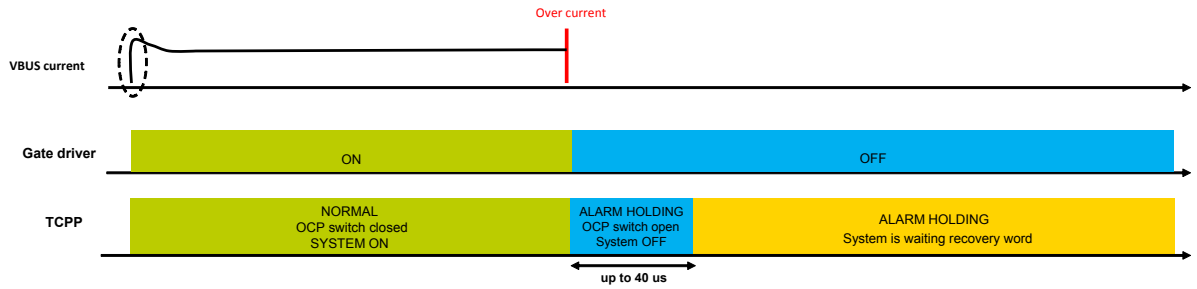
- V<sub>CONN</sub> switches, CC switches and gate drivers are shutting down
- During up to 40 μs typ., this OCP alarm is held (no recovery is possible)
- After this delay, CC switches are turned ON but V<sub>CONN</sub> switches and gate drivers are held OFF

The system can be restarted only with a recovery word sent by the MCU via the I2C bus.

- The FLGn signal stays low as long as the recovery word has not been sent

The recovery word is described in the next paragraph

**Figure 11. Typical chronograms of TCPP03-M20 VBUS OCP**



Note:

- In case of VBUS OCP event, the TCPP03-M20 switches OFF:
  - $V_{CONN}$  switches
  - VBUS gate driver (provider and consumer)
  - $V_{CONN}$  and  $V_{BUS}$  discharge paths are activated
  - CC lines remain active
- It is signaled to the user by several ways:
  - I2C corresponding state bits are cleared (i.e.  $V_{CONN1\_ACK} = 0$ ,  $V_{CONN2\_ACK} = 0\dots$ )
  - I2C relevant OCP flag is set ( $FLGn\_OCP\_VBUS$  is the OCP event coming from VBUS switch for example)
  - Failure flag pin ( $FLGn$ ) is active (i.e. in LowZ state)
- After a delay of up to 40  $\mu s$ , recovery word can be written and the MCU can resume a start-up procedure.

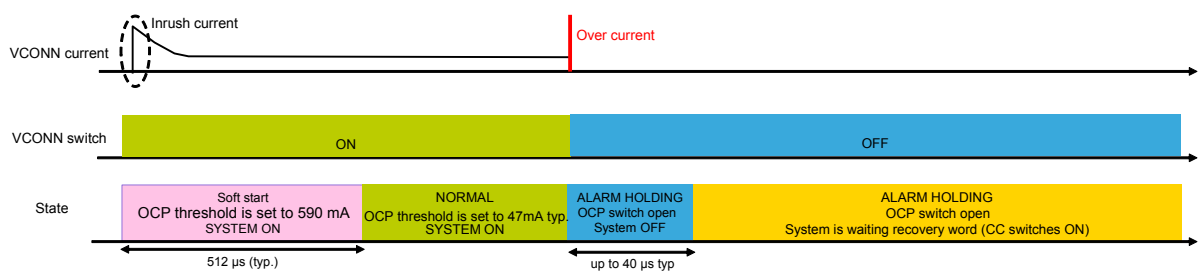
**Table 14. VBUS OCP recovery bit sequence table**

| Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 |
|------|------|------|------|------|------|------|------|
| 0    | 0    | PM2  | PM1  | 1    | 0    | 0    | 0    |

## 7.6 VCONN OCP

- At start-up, a soft start sets the tripping current to about 590 mA during 512  $\mu$ s min. (1ms max.)
- After this delay, the soft start is ended and the normal OCP threshold occurs (50 mA)
- If an OCP event occurs:
  - VCONN switches, CC switches and gate drivers are shutting down
  - During up to 40  $\mu$ s, this OCP alarm is held (no recovery is possible)
  - After this delay, CC switches are turned ON but VCONN switches and gate drivers are held OFF. The system can be restarted only with a recovery word send by the MCU via the I2C bus.
  - The FLGn signal stays low as long as the recovery word has not been sent

Figure 12. VCONN OCP chronograms



After a delay up to 40  $\mu$ s, recovery word can be written and the MCU can resume a start-up procedure.

Table 15. VBUS OCP recovery bit sequence table

| Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 |
|------|------|------|------|------|------|------|------|
| 0    | 0    | PM2  | PM1  | 1    | 0    | 0    | 0    |

## 7.7 VCONN CC line OVP

### 7.7.1 CC lines short to VBUS

USB Type-C standard specifies a pitch of 0.5 mm between connector pins.

VBUS pin being adjacent to the CC pins, when removing the USB Type-C plug from the connector, VBUS can be shorted to CC lines and apply a voltage higher than specified for CC lines.

Over voltage protection is needed on the CC lines because VBUS typical voltage can be as high as 20 V when CC pins are usually 5 V tolerant I/Os on low voltage USB-PHY controllers.

The TCPP03-M20 integrates this protection against CC lines short to VBUS thanks to an overvoltage protection (integrated FET).

When the voltage on the CC line goes above  $V_{TH\_CC}$ , the OVP on CC line turns-on in less than 60ns ( $t_{OVP\_CC}$ ) and FLGn pin goes to '0' state.

When the OVP event disappears, the OVP on the CC line is turned-off and the FLGn pin goes back to 'Hi-Z' state.



## 7.8 VBUS discharge

VBUS discharge is activated via I2C bus and controlled via firmware by the USB-C power delivery controller.

The VBUS discharge feature allows to discharge 10  $\mu$ F in less than 220 ms ( $t_{DIS\_VBUS}$ ).

This discharge time is in line with USB-C specification:

**Table 16. Common source electrical parameters from USB-C specification**

| Parameter | Description                | Min. | Typ. | Max. | Units |
|-----------|----------------------------|------|------|------|-------|
| tSafe0V   | Time to reach vSafe0V max. | -    | -    | 650  | ms    |
| tSafe5V   | Time to reach vSafe5V max. | -    | -    | 275  | ms    |

## 7.9 VCONN discharge

VCONN discharge is activated via I2C bus and controlled via firmware by the USB-C power delivery controller.

The VCONN discharge feature integrated in TCPP03-M20 allows to discharge VCONN in  $R_{DIS\_VCONN} < 5.5 \text{ k}\Omega$ , as per USB-C specification table extracted below:

**Table 17. VCONN source characteristics from USB-C power delivery specification**

| Parameter        | Min.        | Max.          | Notes                                                                                           |
|------------------|-------------|---------------|-------------------------------------------------------------------------------------------------|
| R <sub>dch</sub> | 30 $\Omega$ | 6120 $\Omega$ | Discharge resistance applied in UnattachedWait.SRC between the CC pin being discharged and GND. |

Note:

- *VCONN discharge is activated and stopped via I2C software from USB-PD controller*
- *To avoid short-circuit, VCONN discharge cannot be activated if VCONN switch are closed*
- *The last active CC pin used for VCONN is discharged.*

## 7.10 OTP (over temperature protection)

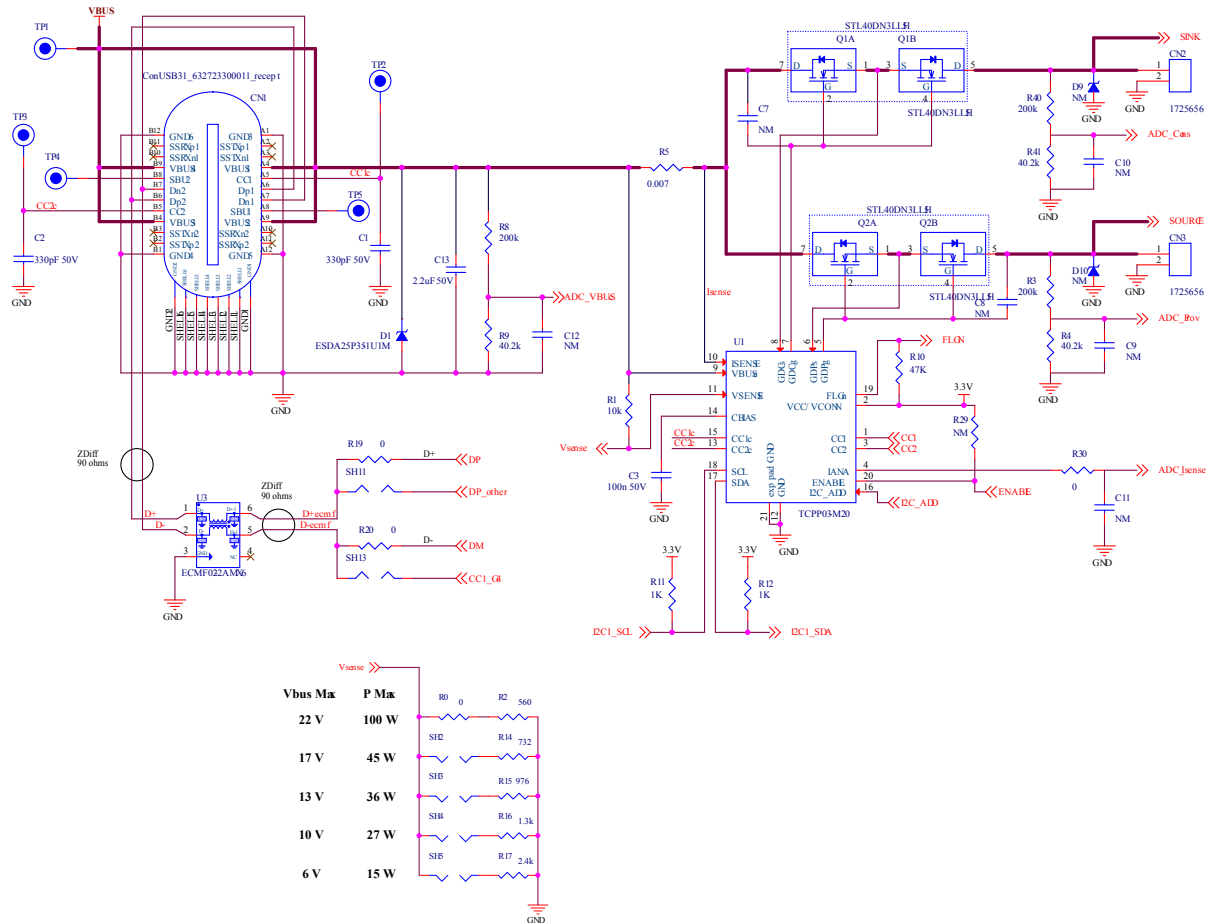
Above 150°C, the OTP triggers the FLGn pin.

OVP and OCP on VCONN, CC lines, VBUS are shut down.

Auto recovery is ensured when the temperature goes back below OTP threshold.

## 8 USB-C dual role power schematic example

Figure 13. Partial schematic extract of nucleo expansion board X-NUCLEO-DRP1M1 using TCPP03-M20



### 8.1 External components description

Table 18. Schematic description

| Component reference                  | Component name or value | Description                                                                                                             |
|--------------------------------------|-------------------------|-------------------------------------------------------------------------------------------------------------------------|
| D1                                   | ESDA25P35-1U1M          | TVS protecting against 25 A 8/20 $\mu$ s surge waveforms and ESD transients (see Transient voltage suppressor on VBUS). |
| C1, C2                               | 330 pF, 25 V            | EMI capacitor, required to comply with USB-C specification.                                                             |
| C3                                   | 100 nF, 50 V            | X7R ESD protection capacitance with low ESL required to comply with USB-C specification.                                |
| C13                                  | 2.2 $\mu$ F, 50 V       | VBUSc bulk capacitance, required in the USB-C power delivery specification.                                             |
| R5                                   | 0.007 $\Omega$          | Serial resistor which value sets the VBUS OCP threshold.                                                                |
| R1<br>R2 or R14 or R15 or R16 or R17 | See Table 12            | Resistor bridge to set VBUS OVP threshold.                                                                              |

## 8.2 Bulk capacitance

USB-C power delivery specification defines cSnkBulk and cSrcBulk capacitances as the sum of bulk capacitances on both sides of the ohmic path of VBUSc.

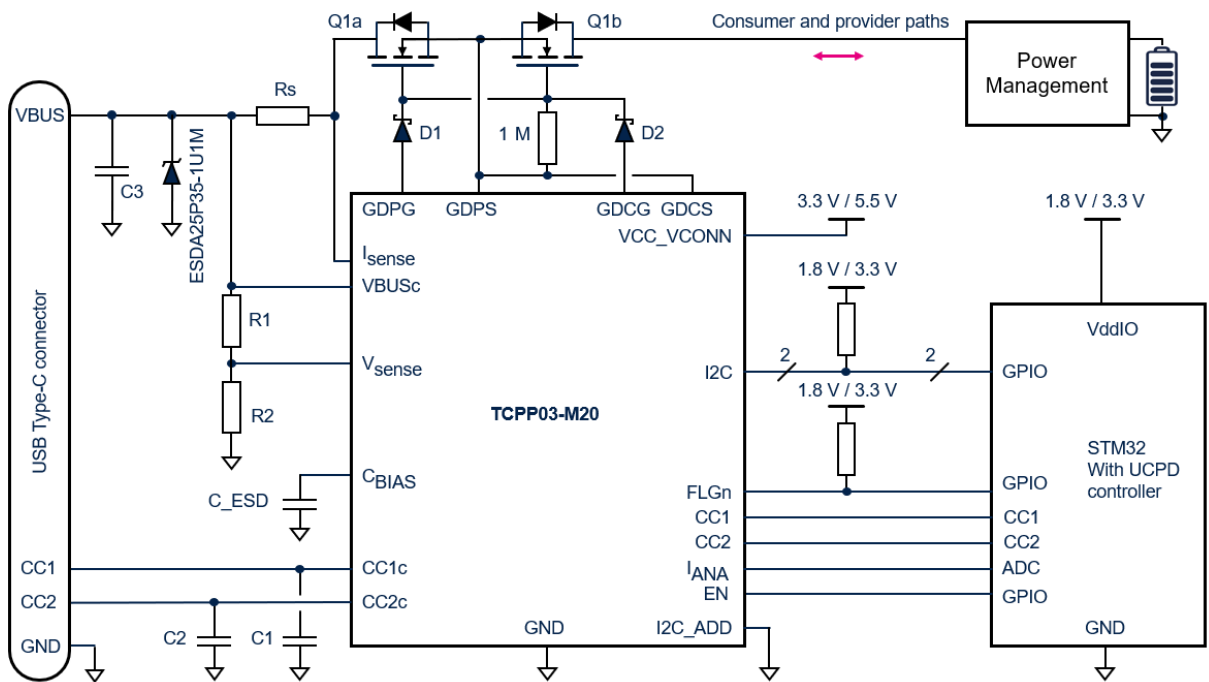
To insure compliance with the standard and TCPP03-M20 protection performances, it is mandatory to place this capacitance on VBUSc, as close as possible to the USB-C connector with a value of 2.2  $\mu\text{F}$  - 50 V.

## 8.3 Single bi-directional power path

Provider and consumer gate drivers are exclusive. To merge consumer and provider paths in a single bi-directional power path, two small signal Schottky diodes (D1, D2) and a 1 M $\Omega$  resistor are needed. OVP / OCP reaction time will be increased to 1 ms. TCPP03-M20 source inputs can be shorted together. Small signal Schottky diodes can either be :

- BAT30CWFILM : 2 diodes in a single SOT-323 package
- BAT30KFILM : 1 diode in a SOD523 package
- BAT30F4 : 1 diode in a ST0201 package

**Figure 14. Bi-directional power path gate drive diagram**



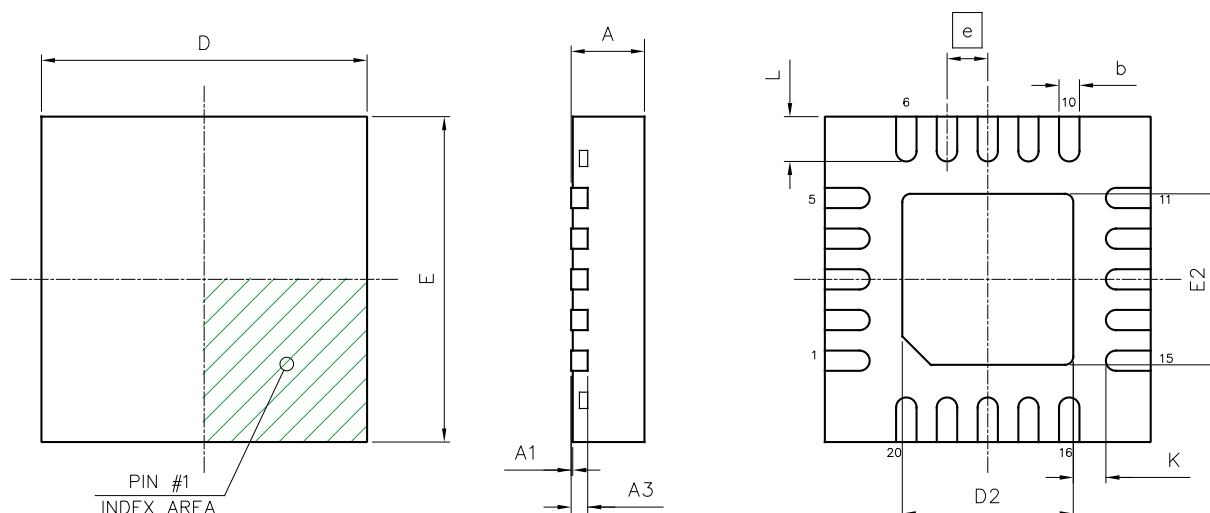
I2C address can either be connected to GND or VddIO with VddIO equal to 1.8 V +/-5% or 3.3 V +/-10%

## 9 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 9.1 QFN-20L package information

**Figure 15. QFN-20L 4.0 x 4.0 x 0.75 mm package outline**



**Table 19. QFN-20L package mechanical data**

| Ref. | Dimensions in millimeters |           |      |
|------|---------------------------|-----------|------|
|      | Min.                      | Typ.      | Max. |
| A    | 0.70                      | 0.75      | 0.80 |
| A1   |                           | 0.02      | 0.05 |
| A3   |                           | 0.20 REF. |      |
| b    | 0.18                      | 0.25      | 0.30 |
| D    | 3.95                      | 4.00      | 4.05 |
| D2   | 1.95                      | 2.10      | 2.20 |
| E    | 3.95                      | 4.00      | 4.05 |
| E2   | 1.95                      | 2.10      | 2.20 |
| e    |                           | 0.50 BSC  |      |
| L    | 0.45                      | 0.55      | 0.65 |
| K    | 0.20                      |           |      |

Figure 16. recommended footprint (dimensions are in mm)

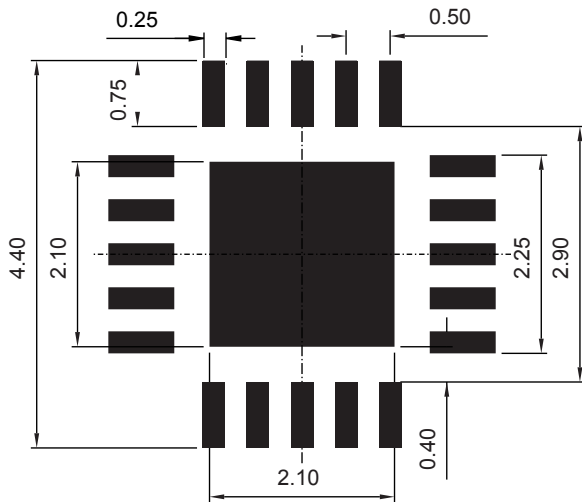


Figure 17. Marking layout

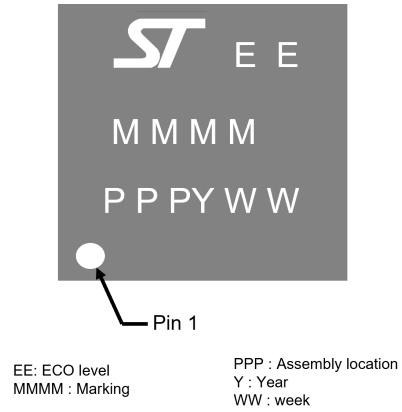
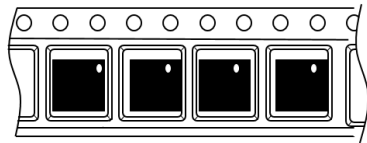


Figure 18. Package orientation in reel



Pin 1 located according to EIA-481

Note: Pocket dimensions are not on scale  
Pocket shape may vary depending on package

Figure 19. Tape and reel orientation

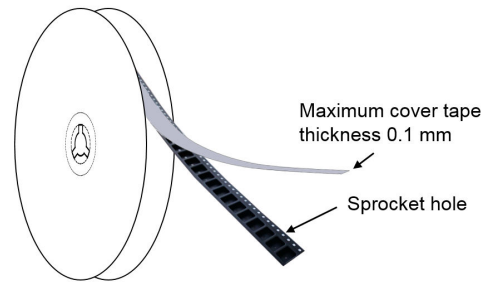


Figure 20. Reel dimensions (mm)

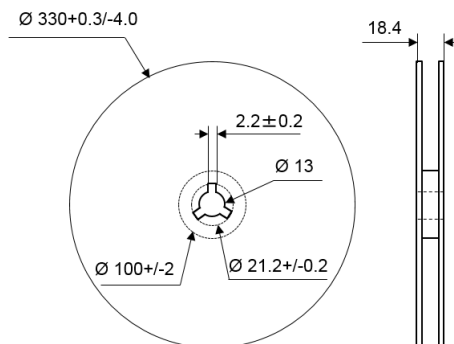


Figure 21. Inner box dimensions (mm)

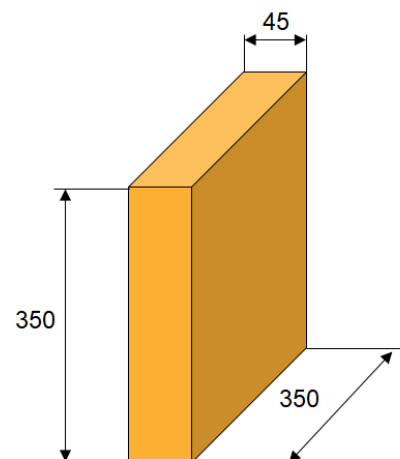
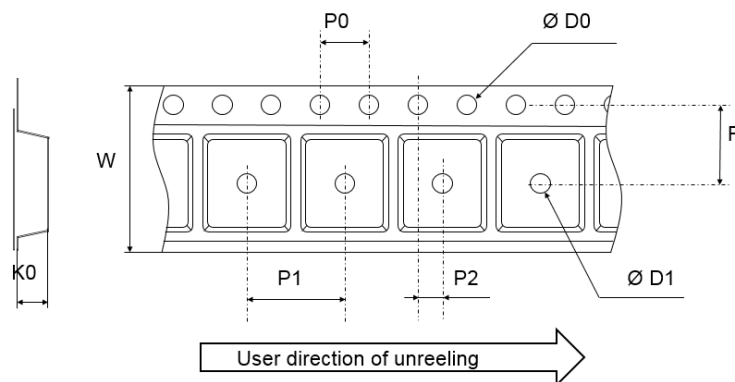


Figure 22. Tape outline



Note: Pocket dimensions are not on scale  
Pocket shape may vary depending on package

Table 20. Tape dimension values

| Ref. | Dimensions  |      |      |
|------|-------------|------|------|
|      | Millimeters |      |      |
|      | Min.        | Typ. | Max. |
| D0   | 1.5         | 1.55 | 1.6  |
| D1   | 1.5         |      |      |
| F    | 5.4         | 5.5  | 5.6  |
| K0   | 1.0         | 1.1  | 1.2  |
| P0   | 3.9         | 4.0  | 4.1  |
| P1   | 7.9         | 8.0  | 8.1  |
| P2   | 1.9         | 2.0  | 2.1  |
| W    | 11.7        | 12   | 12.3 |

## 10 Ordering information

**Table 21. Ordering information**

| Order code | Marking | Package                     | Weight  | Base qty. | Delivery mode |
|------------|---------|-----------------------------|---------|-----------|---------------|
| TCPP03-M20 | TCPP03  | QFN-20L 4.0 x 4.0 x 0.75 mm | 36.1 mg | 3000      | Tape and reel |

## Appendix A Appendix A Reference documents

**Table 22. Reference documents**

| Doc name | ID         | Title                                                   |
|----------|------------|---------------------------------------------------------|
| TA0357   | DM00496853 | Overview of USB Type-C and Power Delivery technologies. |
| AN5225   | DM00536349 | USB Type-C® Power Delivery using STM32 MCUs and MPUs.   |
| AN4871   | DM00294046 | USB Type-C® protection and filtering.                   |
| AN3353   | DM00023467 | IEC 61000-4-2 standard testing.                         |

**Table 23. Associated expansion boards**

| Expansion board | Part number | SW expansion board | USB type-C application                                                              |
|-----------------|-------------|--------------------|-------------------------------------------------------------------------------------|
| X-NUCLEO-SNK1M1 | TCPP01-M12  | X-CUBE-TCPP        | Sink, UFP, consumer                                                                 |
| X-NUCLEO-SRC1M1 | TCPP02-M18  |                    | Source, DFP, provider                                                               |
| X-NUCLEO-DRP1M1 | TCPP03-M20  |                    | DRP, dual role power<br>DRD, dual role data<br>Sink requiring current sense and OCP |

**Table 24. Certifications and tools**

| Reference   | Description                                                                                                                                                                                                                                                   |
|-------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| TID6408     | <a href="https://groups.usb.org/cas/login?service=https%3A//cms.usb.org/casservice%3Fdestination%3D/usb_device/certificate/43767">https://groups.usb.org/cas/login?service=https%3A//cms.usb.org/casservice%3Fdestination%3D/usb_device/certificate/43767</a> |
| wiki.st.com | <a href="https://wiki.st.com/stm32mcu/wiki/Category:USB_Power_Delivery">https://wiki.st.com/stm32mcu/wiki/Category:USB_Power_Delivery</a>                                                                                                                     |
| github.com  | <a href="https://github.com/STMicroelectronics/x-cube-tcpp">https://github.com/STMicroelectronics/x-cube-tcpp</a>                                                                                                                                             |



## Revision history

**Table 25. Document revision history**

| Date        | Revision | Changes                                                     |
|-------------|----------|-------------------------------------------------------------|
| 21-Jun-2021 | 1        | Initial release.                                            |
| 04-Oct-2021 | 2        | Updated Features, <i>Table 6</i> and <i>Table 26</i> .      |
| 01-Jun-2023 | 3        | Added note in <a href="#">Table 5</a> . Minor text changes. |

**IMPORTANT NOTICE – READ CAREFULLY**

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, refer to [www.st.com/trademarks](http://www.st.com/trademarks). All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2023 STMicroelectronics – All rights reserved